

NOT RECOMMENDED FOR NEW DESIGN -NO ALTERNATE PART

ZXM64N02X

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	Ι _D
20V	0.040Ω	5.4A

Description

This new generation of high density MOSFETs from Diodes Incorporated utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

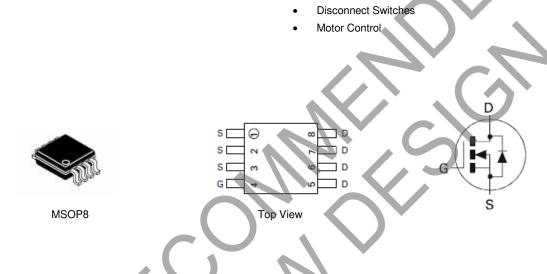
20V N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Low Profile SOIC Package

Applications

- DC DC Converters
- Power Management Functions



Ordering Information

Part Number	Device Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXM64N02XTA	ZXM64N02	7	12mm Embossed	1000 Units
ZXM64N02XTC	ZXM64N02	13	12mm Embossed	4000 Units





Absolute Maximum Ratings

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GS}	± 12	V
Continuous Drain Current ($V_{GS}=4.5V$; $T_A=25^{\circ}C$)(b) ($V_{GS}=4.5V$; $T_A=70^{\circ}C$)(b)	ID	5.4 4.3	Α
Pulsed Drain Current (c)	I _{DM}	30	Α
Continuous Source Current (Body Diode)(b)	I _S	2.4	A
Pulsed Source Current (Body Diode)(c)	I _{SM}	30	A
Power Dissipation at T _A =25°C (a) Linear Derating Factor	PD	1.1 8.8	W mW/°C
Power Dissipation at T _A =25°C (b) Linear Derating Factor	PD	1.8 14.4	W mW/∘C
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

Thermal Resistance

PARAMETER	SYMBOL VALUE UNIT
Junction to Ambient (a)	R _{eJA} 113 °C/W
Junction to Ambient (b)	R _{BJA} 70 °C/W

NOTES

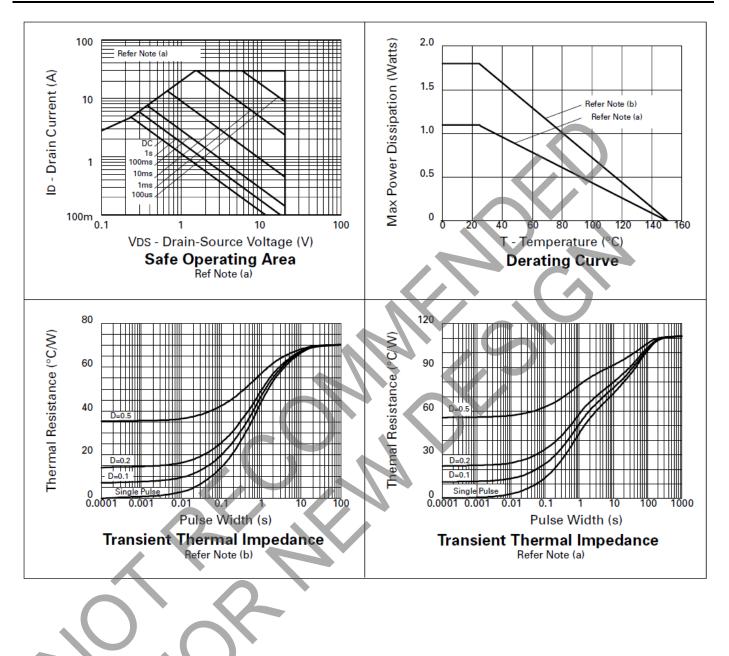
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at t≤10 secs.

(c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.



Typical Characteristics





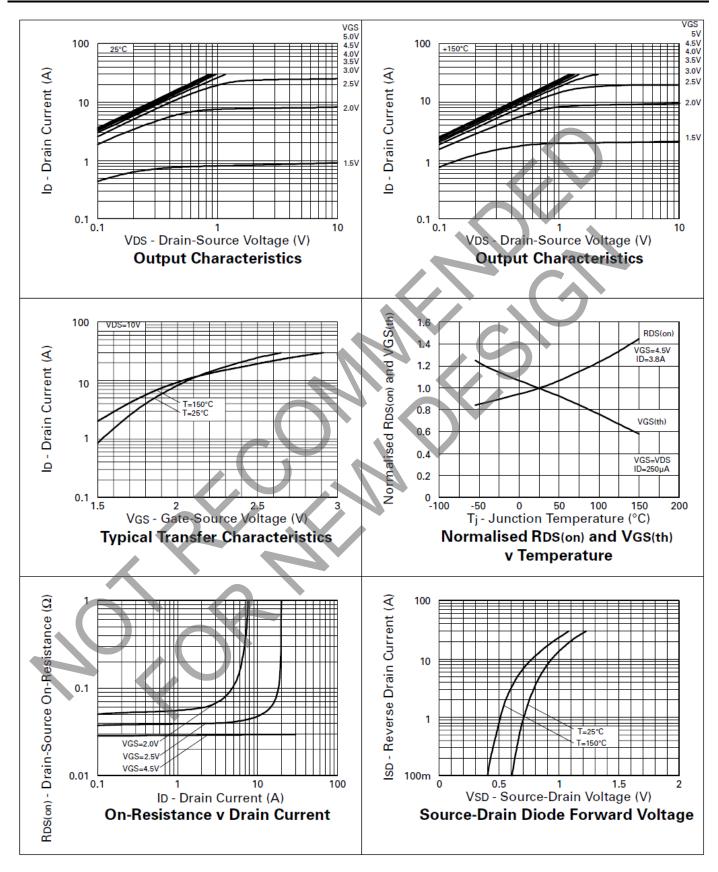
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	20			V	I _D =250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} =20V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	$V_{GS}=\pm 12V, V_{DS}=0V$
Gate-Source Threshold Voltage	V _{GS(th)}	0.7			V	$I_D = 250 \mu A$, $V_{DS} = V_{GS}$
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.040 0.050	Ω Ω	V _{GS} =4.5V, I _D =3.8A V _{GS} =2.7V, I _D =1.9A
Forward Transconductance (3)	g _{fs}	6.1			S	V _{DS} =10V,I _D =1.9A
DYNAMIC (3)						
Input Capacitance	C _{iss}		1100		pF	
Output Capacitance	Coss		350		pF	V _{DS} =15 V, V _{GS} =0V, f=1MHz
Reverse Transfer Capacitance	C _{rss}		100		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	t _{d(on)}		5.7		ns	
Rise Time	t _r		9.6		nŝ	V_{DD} = 10V, I_{D} = 3.8A R _G = 6.2 Ω , R _D = 2.6 Ω (Refer to test circuit)
Turn-Off Delay Time	t _{d(off)}		28.3		ns	
Fall Time	t _f		11.6		ns	
Total Gate Charge	Qg			16	nC	
Gate-Source Charge	Q _{gs}			3.5	nC	V _{DS} =16V,V _{GS} =4.5V, I _D =3.8A (Refer to test circuit)
Gate Drain Charge	Q _{gd}			5.4	nC	
SOURCE-DRAIN DIODE			1		1	1
Diode Forward Voltage (1)	V _{SD}			0.95	V	T _j =25°C, I _S =3.8A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		23.7		ns	T _i =25°C, I _F =3.8A, di/dt= 100A/μs
Reverse Recovery Charge(3)	Q _{rr}		13.3		nC	

(1) Measured under pulsed conditions. Width=300µs. Duty cycle ≤2%.
(2) Switching characteristics are independent of operating junction temperature.
(3) For design aid only, not subject to production testing.



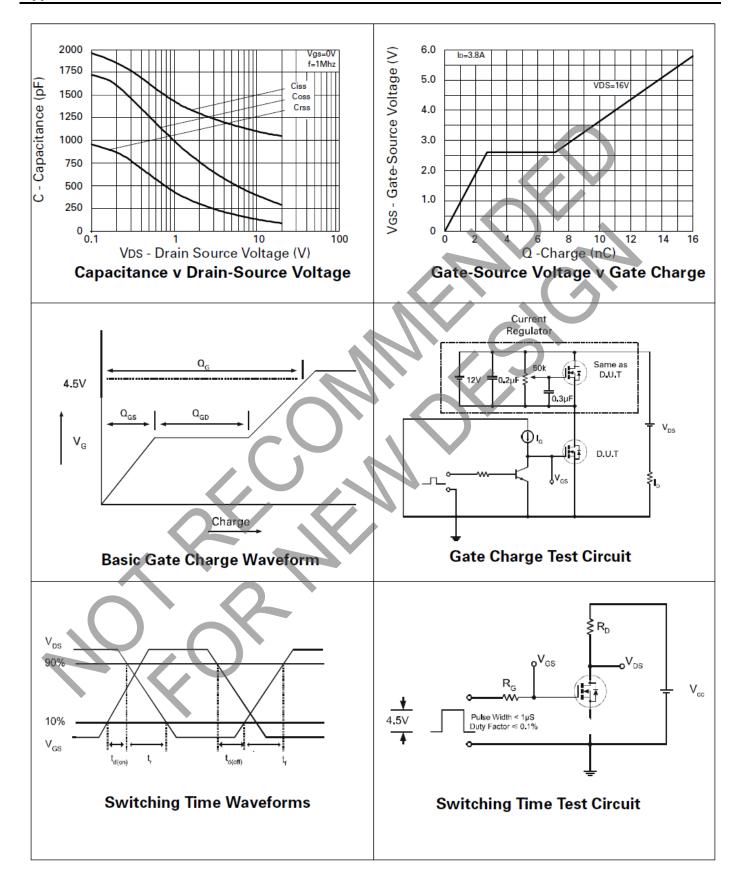
Typical Characteristics





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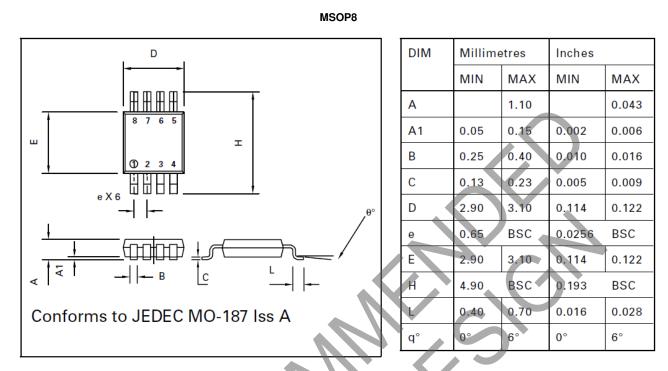
Typical Characteristics (Cont.)





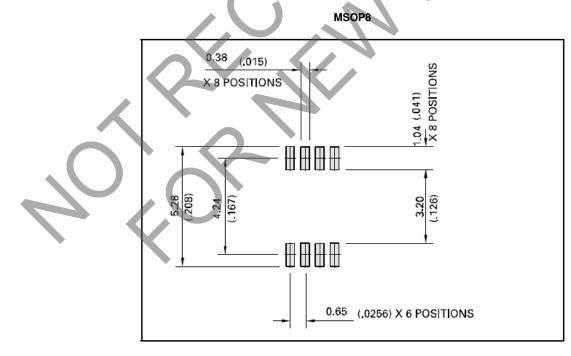
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



Suggested Pad Layout

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